

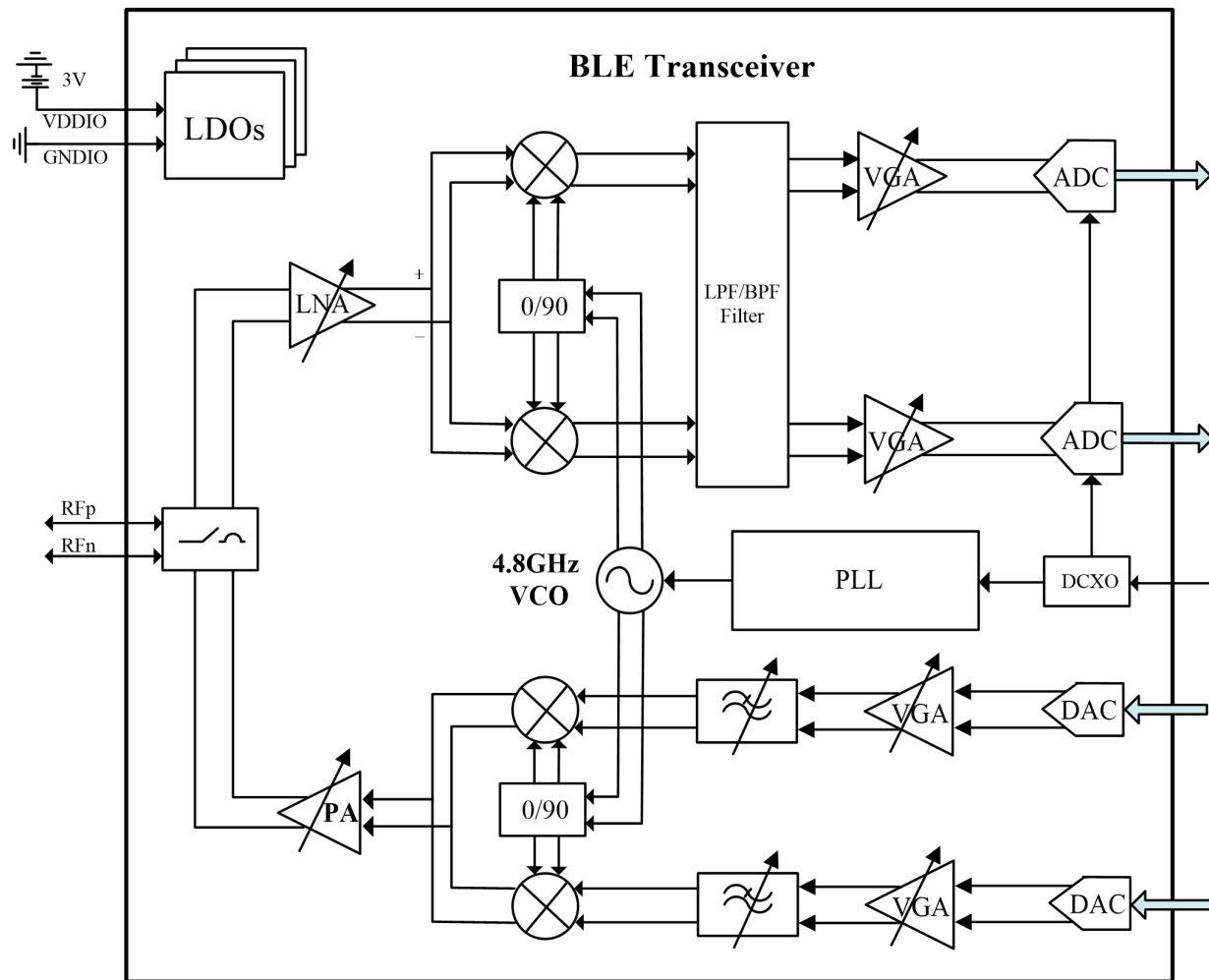
模拟IC设计进阶 课 程 内 容

主讲人：Chris

目录

- 一 低功耗蓝牙 (BLE) Transceiver系统结构介绍
- 二 CMOS工艺有源及无源器件介绍
- 三 g_m/I_d 设计方法介绍及曲线仿真
- 四 Bandgap电路仿真及版图设计
- 五 LDO电路仿真及版图设计
- 六 有源低通滤波器 (LPF) 仿真及版图设计

一、低功耗蓝牙 (BLE) Transceiver系统结构

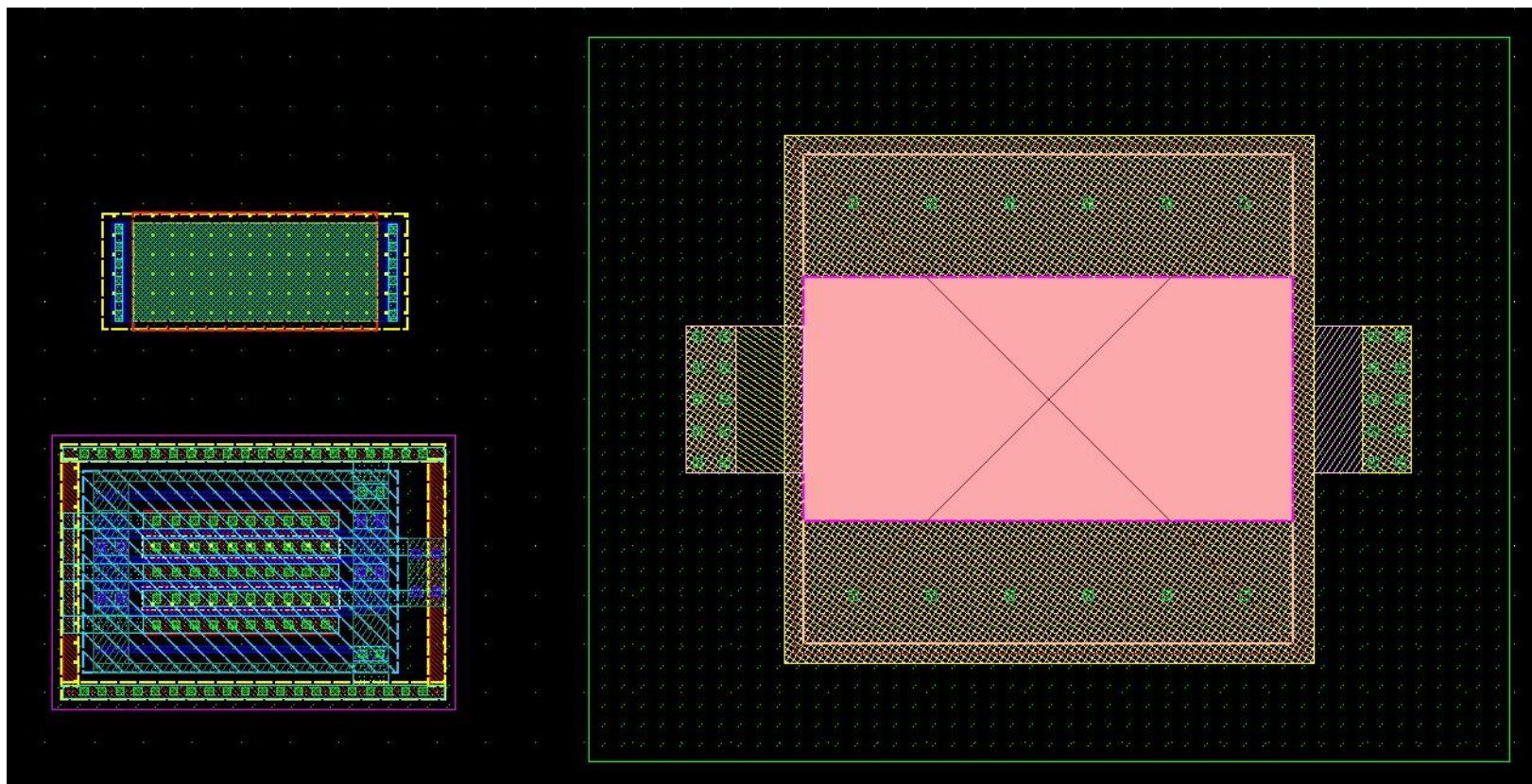


一、低功耗蓝牙（BLE）Transceiver系统结构

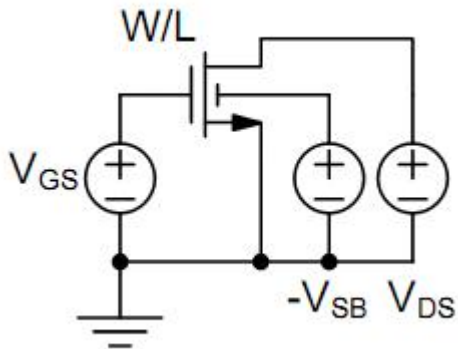
PARAMETER	MIN.	TARGET	MAX.	UNIT	TEST CONDITIONS
RF input frequency range	2402		2480	MHz	
LE Transmitter					
Output RF max power		4		dBm	
RF control range		24		dB	
Coarse gain step		3		dB	
Fine gain step		0.5		dB	
Gain variations	-3		+3	dB	Vs. Process, voltage, temperature
In-band spurious emissions 2MHz			-20	dBm	
In-band spurious emissions, 3MHz or greater			-30	dBm	Standard Measurements conditions ²
LE Receiver					
Receiver Sensitivity		-84		dBm	BER <= 0.1%
Max usable signal	-10			dBm	BER < 0.1%
Co-channel selectivity			21	dB	
Adjacent channel selectivity 1MHz			15	dB	
Adjacent channel selectivity 2MHz			-17	dB	
Adjacent channel selectivity 3MHz			-27	dB	
Image frequency			-9	dB	
Adjacent (1MHz) interference to image			-15	dB	
Out-of-band blocking < 2GHz			-30	dBm	Standard Measurement conditions ²
2.399 – 2.4GHz			-35	dBm	
2.484 – 3.0GHz			-35	dBm	
3.0 – 12.75GHz			-30	dBm	

二、CMOS工艺有源及无源器件介绍

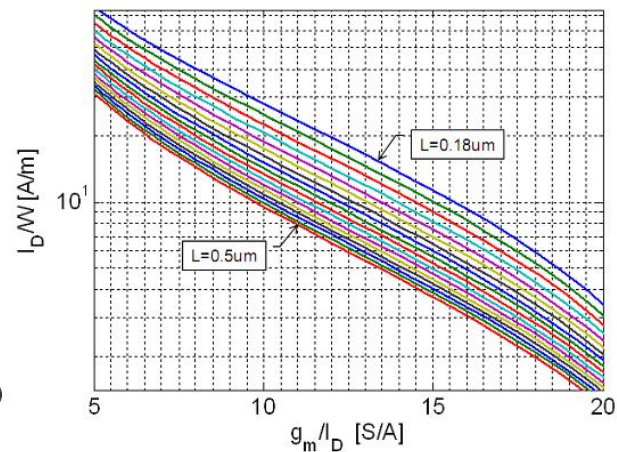
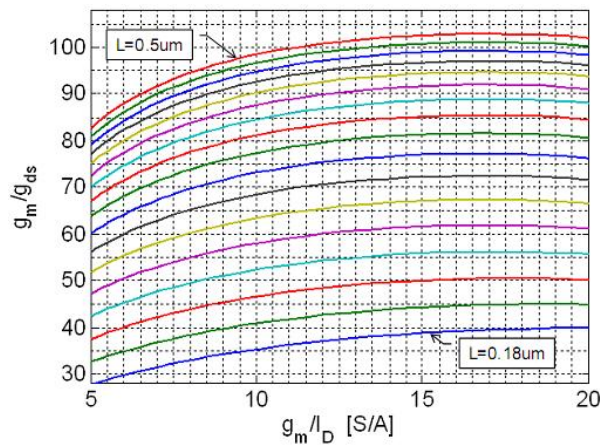
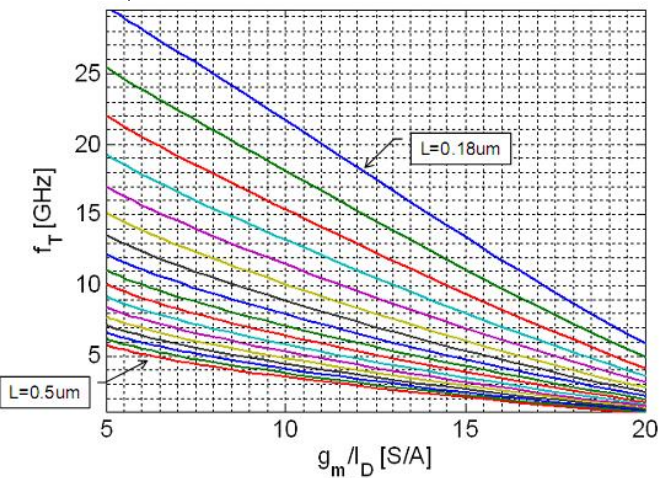
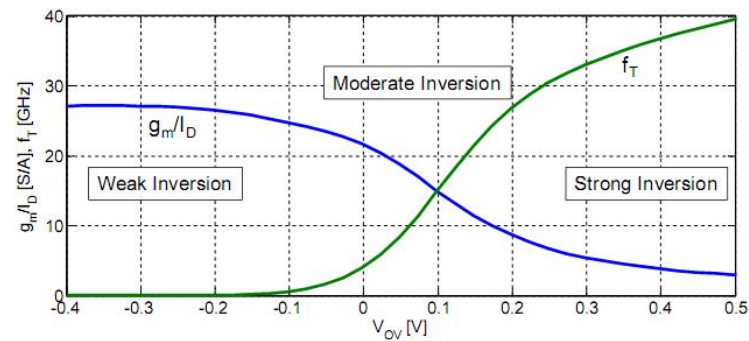
◆ MOS晶体管、BJT、电阻、电容、电感等



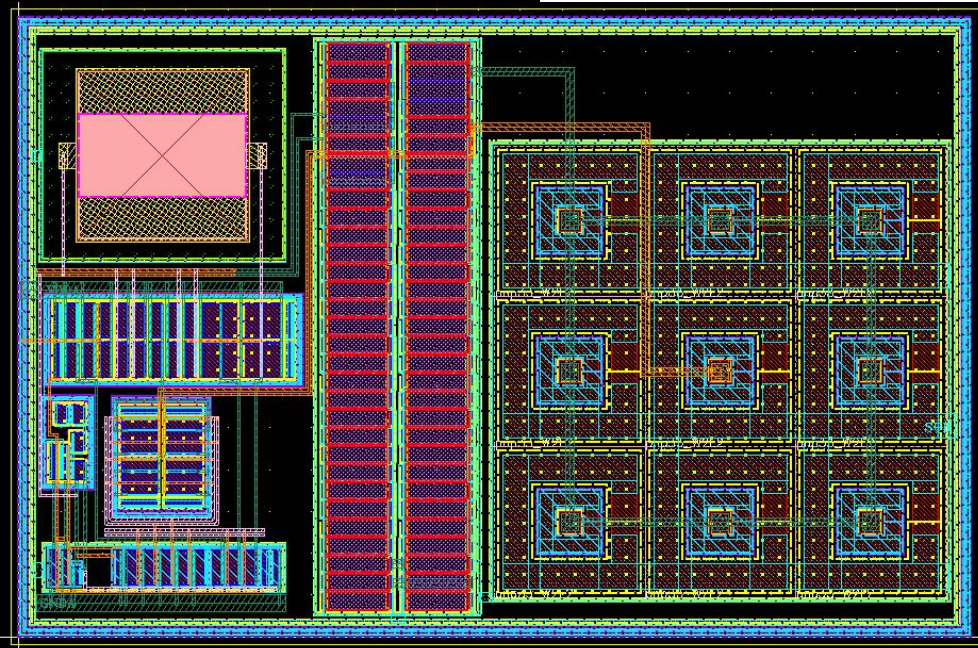
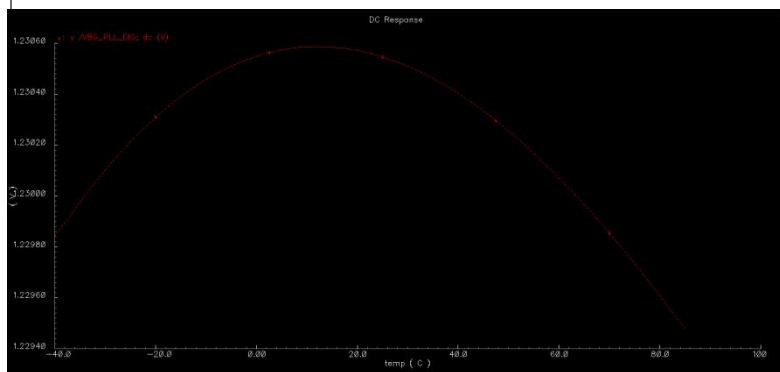
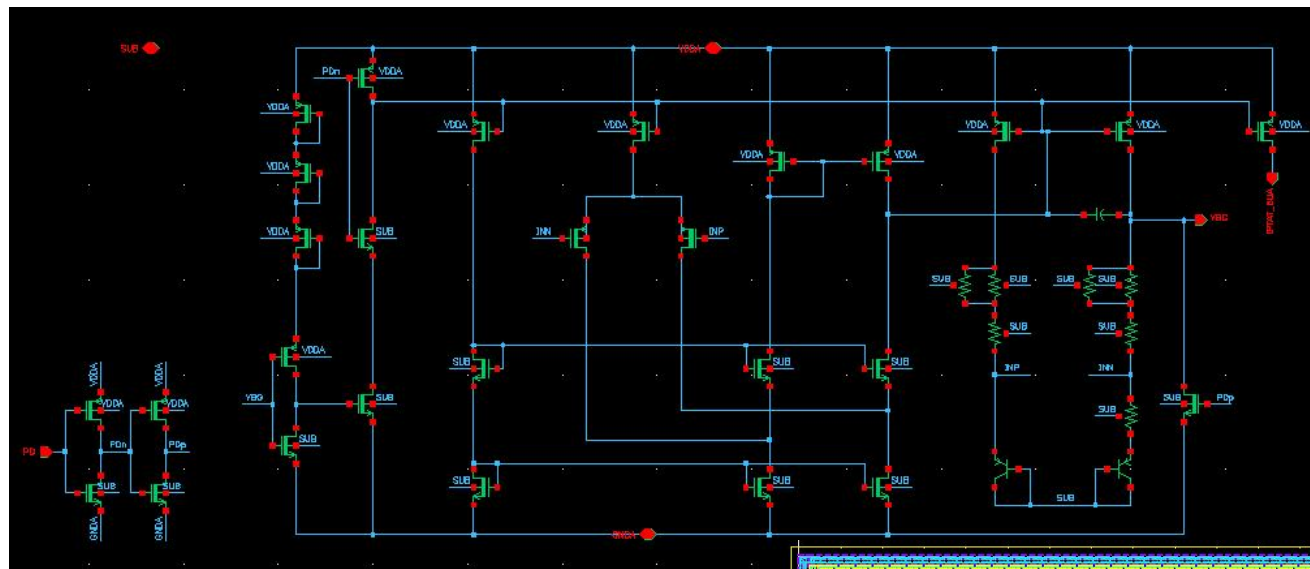
三、 g_m/I_D 设计方法介绍及曲线仿真



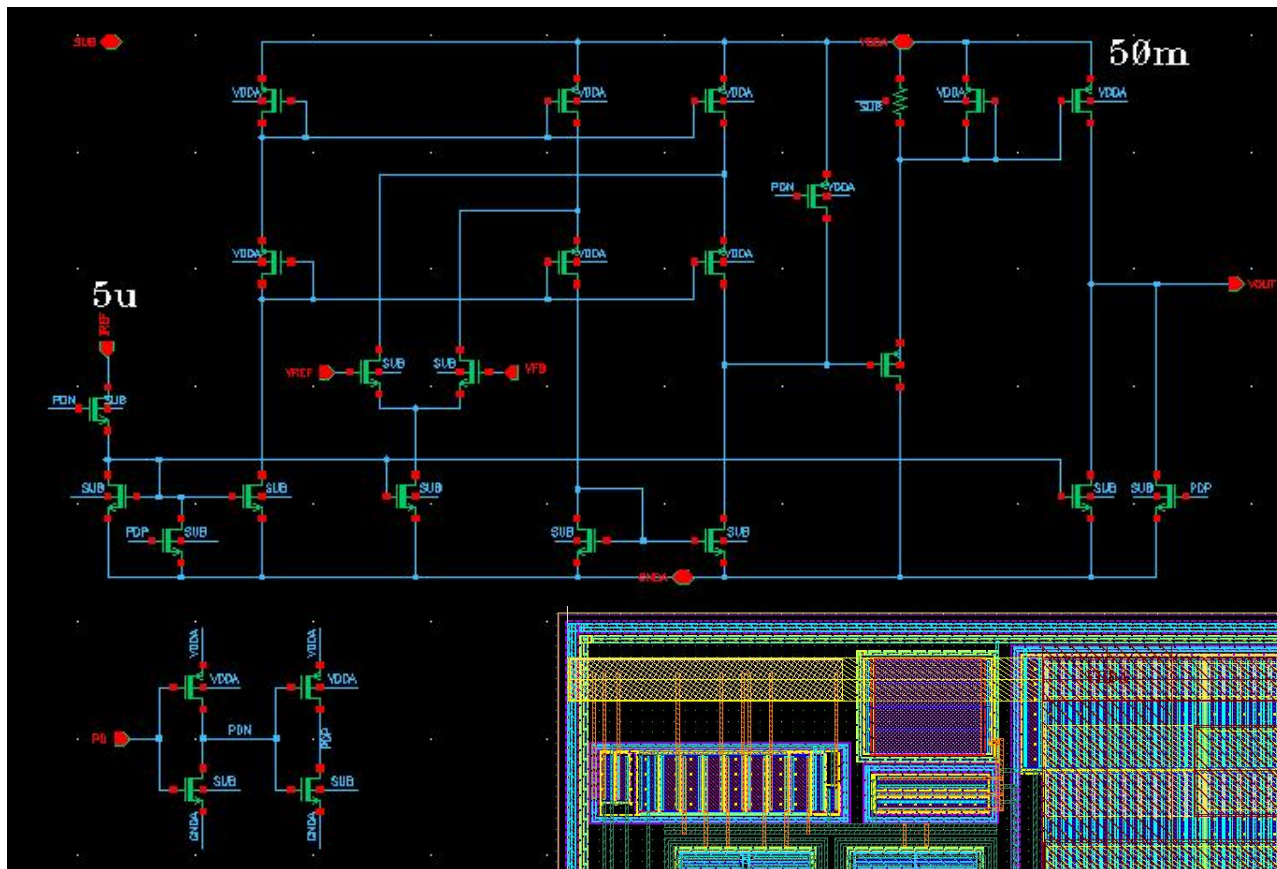
Design Tradeoff: g_m/I_D and f_T



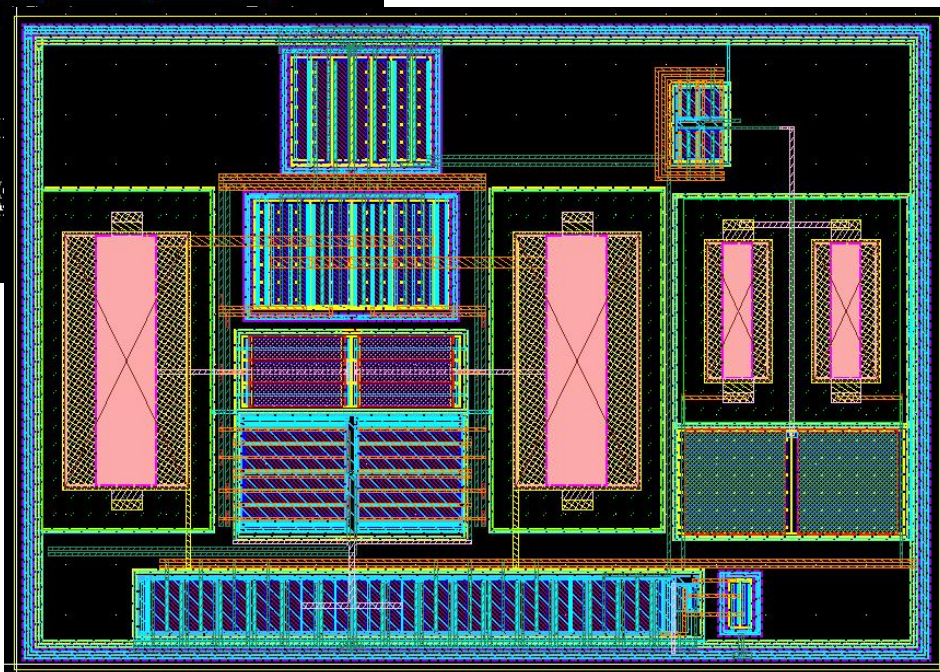
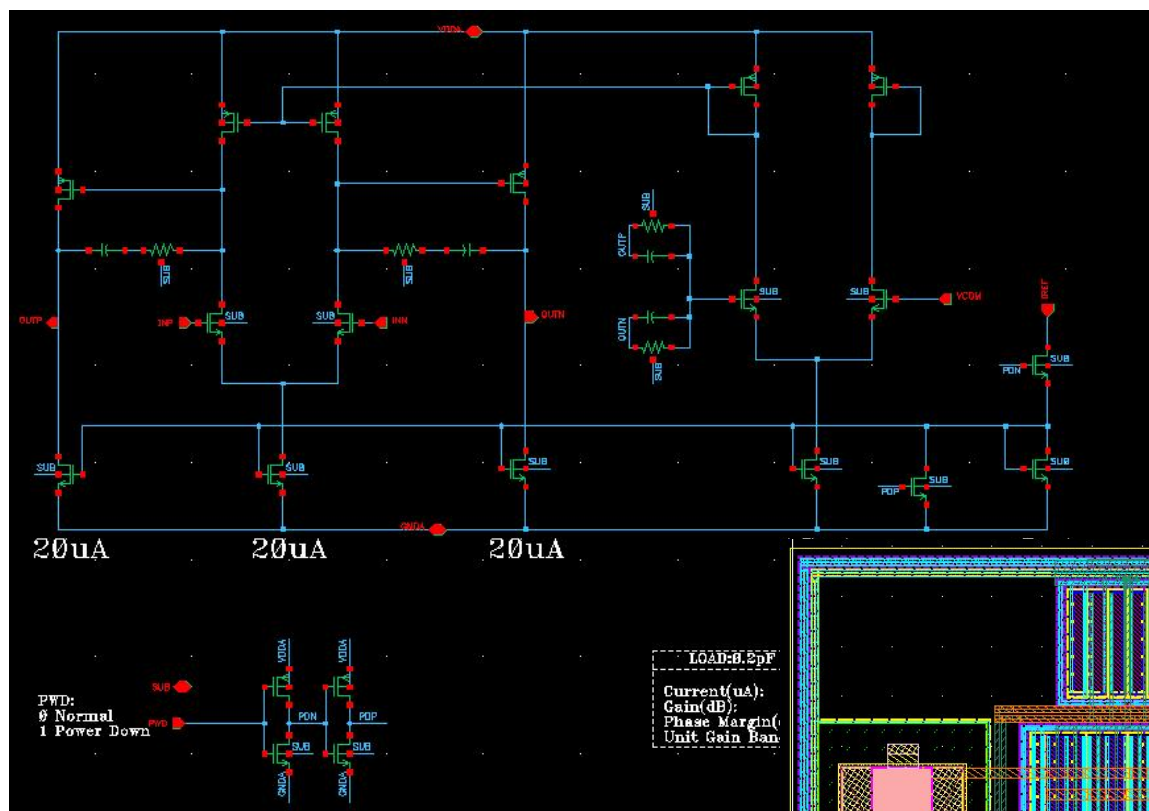
四、Bandgap电路仿真及版图设计



五、LDO电路仿真及版图设计



六、有源低通滤波器 (LPF) 仿真及版图设计



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